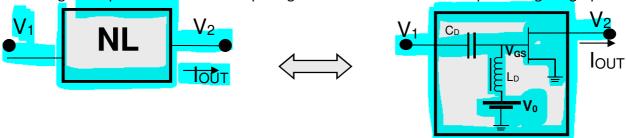


## E(rasmus) Mundus on Innovative Microwave Electronics and Optics Master



## **Tutorial (SEM cold-FET Mixer)**

The following cold-FET mixer (biased @  $V_{DSO}=0$  V) is used to design a SEM up-converter where the LO signal  $V_1$  is applied to the gate, which is biased @ ( $V_{GSO}=V_0$ ) while the IF input signal is applied to the drain using a low-pass filter and the output signal is extracted at the drain port using a high-pass filter.



The nonlinear operation of the cold-FET (NL) is expressed by the 2 following equations that give the output current  $I_{OUT}$  as a function of input and output control voltages  $V_1$  and  $V_2$ :

$$V_{GS} = V_0 + V_1$$
 (eq1)  
 $I_{OUT} = p V_2 - q V_2 V_{GS}^2 + r V_1$  (eq2)

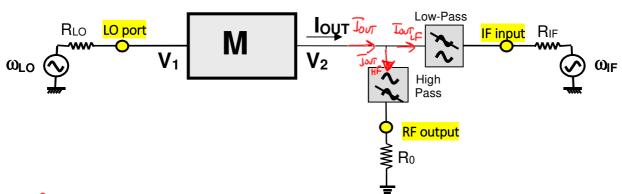
where  $V_0$  is a constant (gate bias voltage)

where  $\boldsymbol{p}$  ,  $\boldsymbol{q}$  and  $\boldsymbol{r}$  are constants

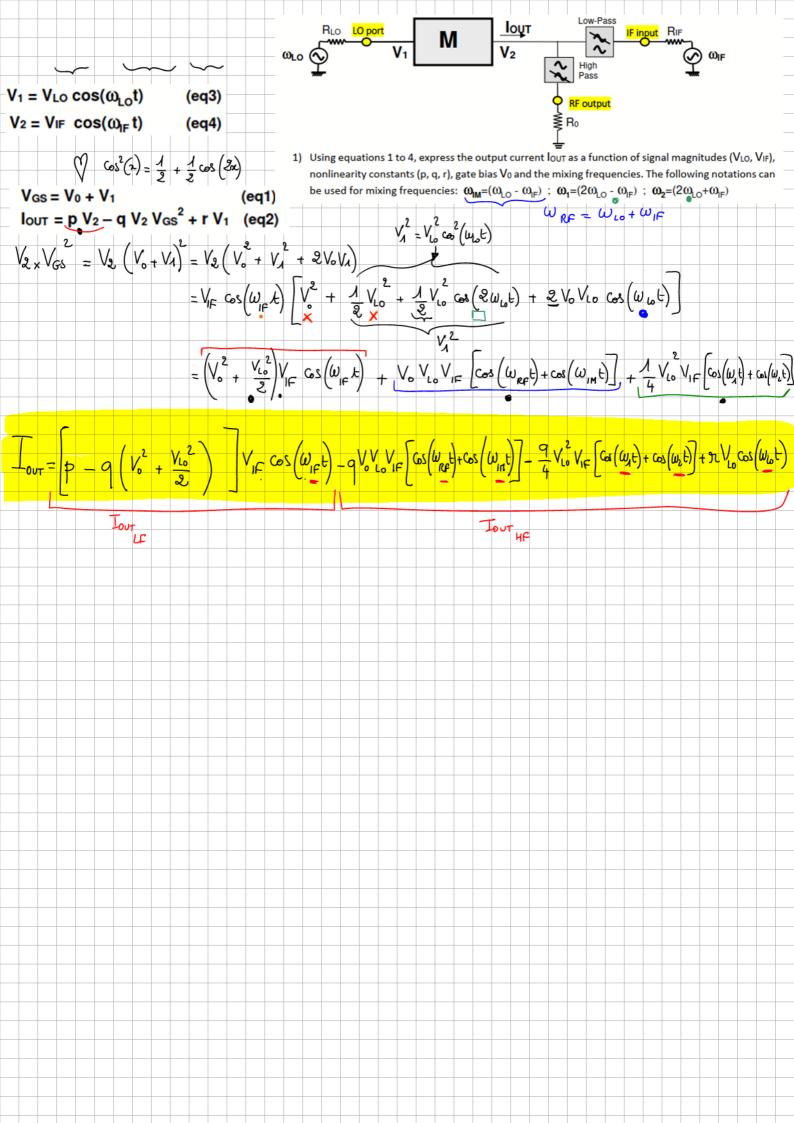
The SEM cold-FET mixer is shown below and the main frequencies are :  $f_{LO}$  = 9 GHz ,  $f_{IF}$  = 0.5 GHz et  $f_{RF}$  =  $f_{LO}$  +  $f_{IF}$  = 9.5 GHz ( $\omega_{RF}$  =  $\omega_{LO}$  +  $\omega_{IF}$ ).

The two control voltages  $V_1$  and  $V_2$  of the FET mixer are :

- LO voltage at gate port :  $V_1 = V_{LO} \cos(\omega_{LO}t)$  (eq3)
- IF voltage at drain port :  $V_2 = V_{IF} \cos(\omega_{IF} t)$  (eq4)



- 1) Using equations 1 to 4, express the output current  $I_{OUT}$  as a function of signal magnitudes ( $V_{LO}$ ,  $V_{IF}$ ), nonlinearity constants (p, q, r), gate bias  $V_0$  and the mixing frequencies. The following notations can be used for mixing frequencies:  $\omega_{IM} = (\omega_{LO} \omega_{IF})$ ;  $\omega_1 = (2\omega_{LO} \omega_{IF})$ ;  $\omega_2 = (2\omega_{LO} + \omega_{IF})$
- 2) The high-pass filter is designed to reject frequencies lower than 5GHz while the low-pass frequency is designed to cut frequencies greater than 5GHz. Therefore, what are the mixing frequencies at the RF output port?
- 3) Determine the expression of the voltage conversion gain  $G_{\text{CV}}$ .
- 4) If the LO port is assumed to be matched to  $R_{LO}$ ,
  - a) express the LO power applied at the LO port
  - b) express the LO power at the RF output port
  - c) express in dB the LO-to-RF isolation
  - d) what is the LO-to-IF isolation?
  - e) express the equivalent impedance  $Z_{IN}$  seen by the IF generator @  $\omega_{IF}$  at the IF input port



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